

Shottky barrier diode

RB160M-30

●Application

General rectification.

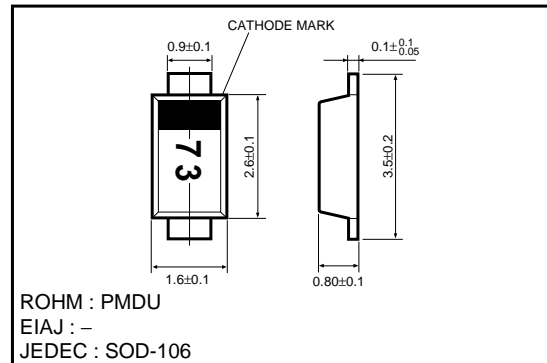
●Features

- 1) Small power mold type (PMDU).
- 2) High reliability.
- 3) Low V_F .

●Structure

Silicon Epitaxial Planer

●External dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	30	V
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_O	1	A *
Forward current surge peak (60Hz / 1cyc.)	I_{FSM}	30	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to 125	°C

* Glass epoxy substrate at the time of assembler, half sine wave at 180°.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	-	0.39	0.460	V	$I_F=0.5A$
	V_{F2}	-	0.43	0.480	V	$I_F=1.0A$
Reverse current	I_{R1}	-	3.0	20	μA	$V_R=15V$
	I_{R2}	-	9.0	50	μA	$V_R=30V$

*Please pay attention to static electricity when handling.

Diodes

●Electrical characteristic curves (Ta=25°C)

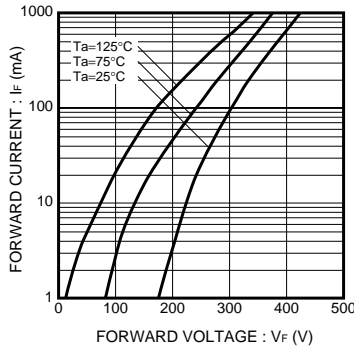


Fig.1 Forward Characteristics

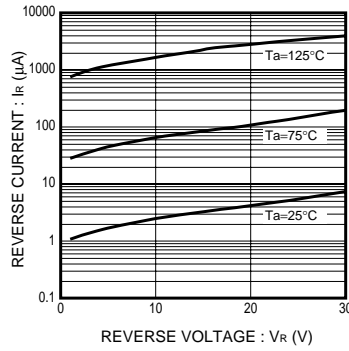


Fig.2 Reverse Characteristics

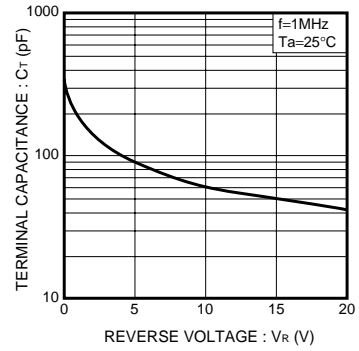


Fig.3 Capacitance Between Terminals Characteristics

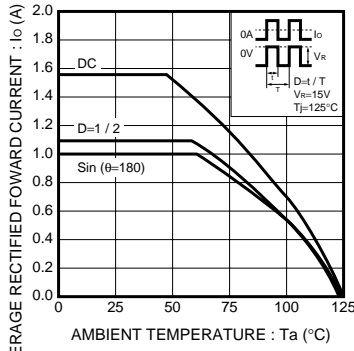


Fig.4 Derating Curve (Io-Ta)

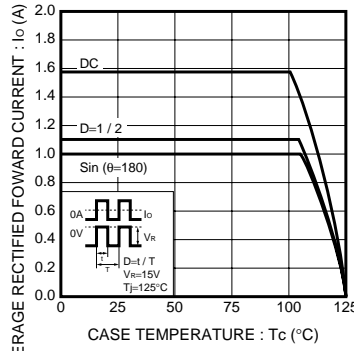


Fig.5 Derating Curve (Io-Tc)

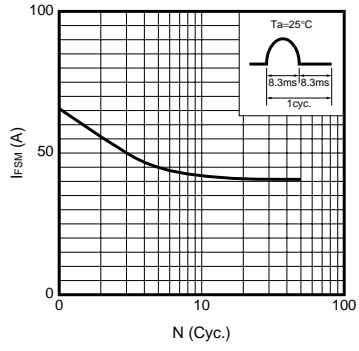


Fig.6